

FLK012WF

X-Ku Band Power GaAs FETs

ABSOLUTE MAXIMUM RATINGS (Ambient Temperature $T_a = 25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c=25^\circ\text{C}$	1.15	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain - source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed +0.25 and -0.05 mA respectively with gate resistance of 3000 Ω .

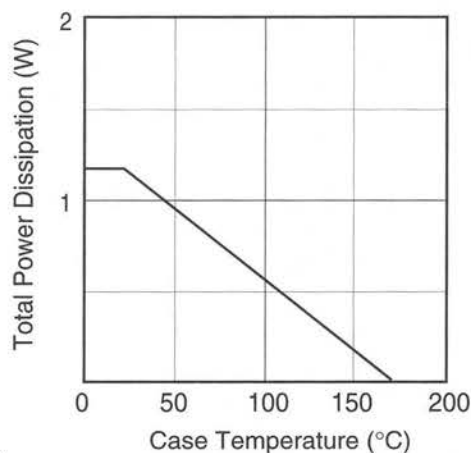
ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a = 25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	60	90	mA
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 40\text{mA}$	-	30	-	mS
Pinch-off Voltage	V_P	$V_{DS} = 5\text{V}, I_{DS} = 3\text{mA}$	-1.0	-2.0	-3.5	V
Gate-Source Breakdown Voltage	V_{GSO}	$I_{GS} = -3\ \mu\text{A}$	-5	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.6 I_{DSS} (\text{Typ.}),$ $f = 14.5\text{GHz}$	19.5	20.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		6.0	7.5	-	dB
Power added Efficiency	η_{add}		-	26	-	%
Noise Figure	NF	$V_{DS} = 3\text{V},$ $I_{DS} = 20\text{mA} (\text{Typ.}),$ $f = 12\text{GHz}$	-	2.5	-	dB
Associated Gain	G_{as}		-	7	-	dB
Thermal Resistance	R_{th}	Channel to Case	-	65	130	$^\circ\text{C/W}$

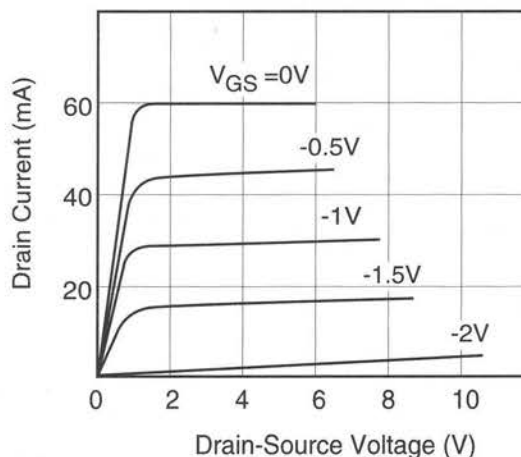
CASE STYLE: WF

G.C.P: Gain Compression Point

POWER DERATING CURVE

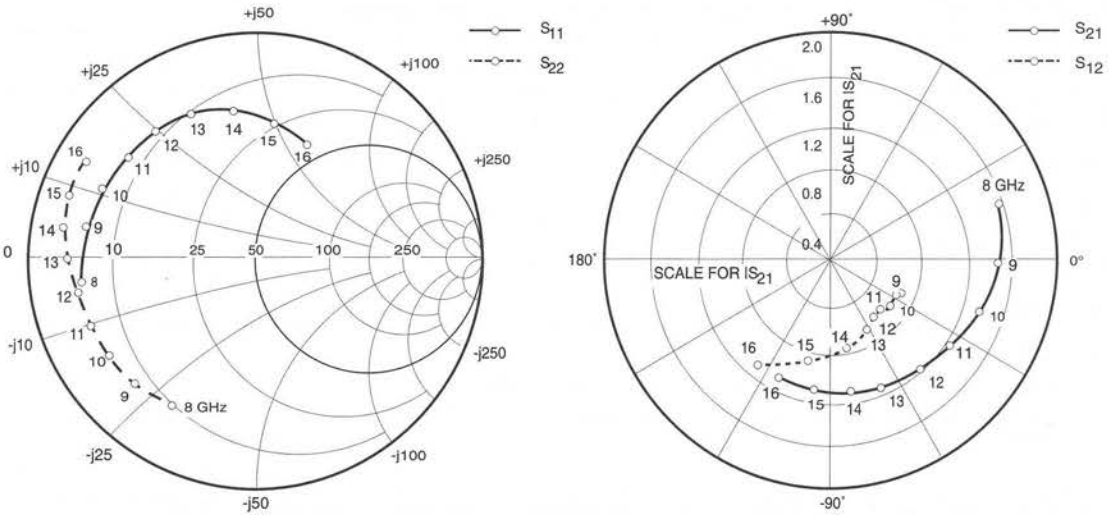


DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



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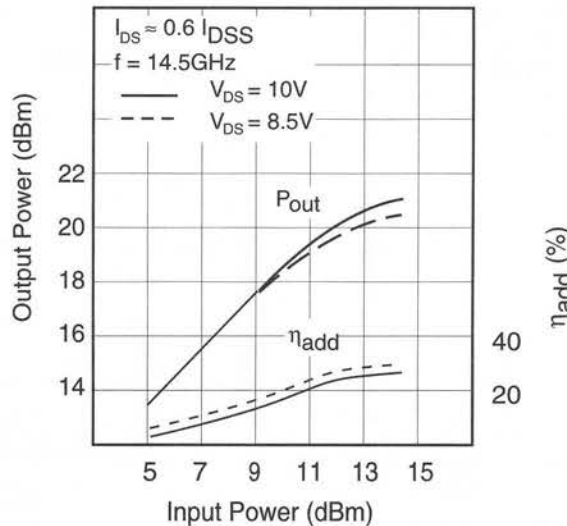


S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 40mA$

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
500	.992	-13.0	2.474	167.9	.007	78.0	.797	-8.6
1000	.985	-25.1	2.454	156.7	.014	69.9	.794	-16.2
8000	.804	-173.9	1.566	15.8	.037	-23.4	.760	-119.1
9000	.793	169.8	1.447	-1.7	.035	-28.1	.785	-132.5
10000	.770	154.9	1.335	-18.1	.033	-37.5	.797	-145.4
11000	.755	140.6	1.237	-33.5	.031	-43.7	.804	-158.0
12000	.745	127.3	1.170	-48.6	.030	-51.4	.814	-169.4
13000	.726	113.6	1.129	-64.4	.033	-64.1	.838	-180.0
14000	.684	99.8	1.094	-80.6	.037	-80.4	.864	170.3
15000	.617	83.8	1.078	-97.9	.044	-102.9	.875	159.8
16000	.535	65.7	1.074	-116.4	.056	-126.5	.866	149.0

OUTPUT POWER vs. INPUT POWER



FUJITSU

Case Style "WF" Metal-Ceramic Hermetic Package

